

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13116	((257/288) or (257/e29.195) or (250/287) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563)).OCLS	US-PGRUB; USPAT; USOCR; FPRS; EPC; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/16 10:01
L2	144	1 and (varact? variable adj (capacitor capacitance) gated adj diode)	US-PGRUB; USPAT; EPC; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:02
L3	1	method near4 (amplifying amplification amplify) near4 signal.clm. and signal adj line.clm. and (biterminal two-terminal ("two" near1 terminals) gated adj diode diode).clm. and isolation near1 (device structure component).clm.	US-PGRUB; USPAT; EPC; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:14
L4	1	((luk).in. (denard).in. (ibm (international adj business)).as.) and method near4 (amplifying amplification amplify) near4 signal.clm. and signal adj line.clm. and (biterminal two-terminal ("two" near1 terminals) gated adj diode diode).clm. and isolation near1 (device structure component).clm.	US-PGRUB; USPAT; EPC; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 10:15
S1	3	*751714*.ap.	US-PGRUB; USPAT; EPC; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/06 14:01
S2	13	miller near2 compensating adj capacitor	US-PGRUB; USPAT; EPC; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 14:41
S3	4	*751713*.ap.	US-PGRUB; USPAT; EPC; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 14:44

S4	0	gated adj diode and (nonlinear variable) near3 "capacitance."	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:45
S5	7	gated adj diode and (nonlinear variable) near3 capacitance	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:46
S6	2	gated adj diode and (nonlinear variable) near3 capacitance and (applying amplification amplifier)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:16
S7	6	gated adj diode and (nonlinear variable vary) near3 capacitance and (applying amplification amplifier)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:20
S8	6	gated adj diode and (nonlinear variable vary) near3 capacitance and (applying amplification amplifier amplify)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:27
S9	3	gated adj diode near4 amplifier	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:50
S10	33	small adj signal adj sensing and dram	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:52
S11	0	fated adj diode.ti.ab,dm. and "257"/\$7.cds.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:52

SI2	83	gated adj diode.ti.ab,clm. and "257"/\$7.ccls.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:54
SI3	31	gated adj diode.ti. and "257"/\$7.ccls.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 16:03
SI4	148	(257/312).CCLS.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:11
SI5	4	MOSFET near5 body adj bias.ti.ab,clm.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 16:15
SI6	100	flash adj memory adj cell adj array and "257"/\$7.ccls.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 16:45
SI7	24	flash adj memory adj cell adj array.ti.ab,clm. and "257"/\$7.ccls.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 16:45
SI8	4	"751714".ap.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:09
SI9	1	(US-20060146895-5).did.	US-PGRUB	OR	OFF	2005/08/26 07:09
SI20	4	"571713".ap.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:10

S21	5	"751713".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:10
S22	1	(US-20050146928-\$).did.	US-PGPUB	OR	OFF	2005/08/26 07:11
S23	175	variable near2 (capacitor capacitance) and sense adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:12
S24	398	(varying varies vary variable) near2 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:15
S25	296	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:29
S26	258	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and (gate control adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:29
S27	255	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:32
S28	183	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:34
S29	143	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor) same (capacitor capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:36

S30	60	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor) same (capacitor capacitance) same ("well" "n-well" "p-well" nwell pwell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:37
S31	25	(variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor) same (capacitor capacitance) same ("well" "n-well" "p-well" nwell pwell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:38
S32	10	(US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$ or US-20050104119-\$ or US-20050104118-\$ or US-20050099859-\$ or US-20030206437-\$).did. or (US-6731529-\$ or US-6418044-\$ or US-6414862-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/08/26 07:42
S33	13	diario.in. and variable adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:20
S34	10	(US-20030206437-\$ or US-20050099859-\$ or US-20050104118-\$ or US-20050104119-\$ or US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$).did. or (US-6414862-\$ or US-6418044-\$ or US-6731529-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/08/26 08:34
S35	2	("6144581").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:36
S36	0	("gatedadjdiodeandvariableadj(capacitancecapacitor)and (MOSadjtransistorMOSFETFETMISadjtransistorMISFET)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:37
S37	2	gated adj diode and variable adj (capacitance capacitor) and (MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:43
S38	3	gated adj diode and (varactor variable adj (capacitance capacitor)) and (MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:44

S39	3	gated adj diode and (varactor variable adj (capacitance capacitor)) and (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:44
S40	3	gated near1 diode and (varactor variable adj (capacitance capacitor)) and (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:46
S41	846	(varactor variable adj (capacitance capacitor)) near10 (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:46
S42	536	(varactor variable adj (capacitance capacitor)) near4 (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:46
S43	11	(varactor variable adj (capacitance capacitor)) near4 (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET) and sense adj amplifier	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:57
S44	1942	((365/207) or (365/208)).COLS.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:57
S45	1609	S44 and sense adj amplifier	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:58
S46	0	S44 and sense adj amplifier and gated adj diode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:58

S47	6	S44 and sense adj amplifier and (varactor capacitor near4 variable)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 09:07
S48	2	("5844265").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 09:54
S49	57	gated adj diode near6 ("well" "n-well" "p-well" pwell nwell)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 09:55
S50	52	gated adj diode near4 ("well" "n-well" "p-well" pwell nwell)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 10:09
S51	2	("6674116").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 10:10
S52	1	S51 and "well"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 10:10
S53	0	("well" nwell pwell) near4 gated adj diode near10 vary near2 capacitance	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 10:12
S54	10	("well" nwell pwell) near4 (varactor gated adj diode) near10 vary near2 capacitance	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:09

S55	108	cascode near4 protect\$3	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:10
S56	935	cascode.tl.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:10
S57	8	cascode.tl. and protect\$3.tl.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:11
S58	8	cascode.tl. and protect\$3.tl. and cascode	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:11
S59	1	"5844265".pn. and (threshold protect\$3)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 13:37
S60	10	"sample/hold" near4 latch	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 16:20
S61	15	(US-20030208437-\$ or US-20050099859-\$ or US-20050104118-\$ or US-20050104119-\$ or US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$).did. or (US-5838176-\$ or US-5844265-\$ or US-6097432-\$ or US-6414862-\$ or US-6418044-\$ or US-6674116-\$ or US-6731529-\$ or US-6794707-\$).did.	US-PGRUB; USPAT	OR	OFF	2005/08/26 16:33
S62	9	S61 and overlap\$4	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 16:37



S63	2	gated adj diode near4 (overlap overlapping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:38
S64	10	mos adj capacitor near4 (overlap overlapping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:40
S65	10	mos adj capacitor near4 (overlap overlapping) and (overlap overlapping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:44
S66	21	mos adj capacitor.ti.ab. and gate near4 (overlap overlapping) and (overlap overlapping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:48
S67	27	(gate adj diode mos adj capacitor).ti.ab. and gate near4 (overlap overlapping) and (overlap overlapping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:49
S68	6	(gate adj diode).ti.ab. and gate near4 (overlap overlapping) and (overlap overlapping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:49
S69	74	(gated adj diode varactor variable adj capacitor) and sense adj amplifier and invert?r	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:31
S70	18	(gated adj diode) and sense adj amplifier and invert?r	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:14

S71	34	(varactor) and sense adj amplifier and invert?	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:15
S72	25	(variable adj capacitor) and sense adj amplifier and invert?	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:15
S73	10	(gated adj diode varactor variable adj capacitor) and sense adj amplifier and invert? and control adj line and signal adj line	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:31
S74	9	(gated adj diode varactor variable adj capacitor) and sense adj amplifier and invert? and control adj line and signal adj line and (opamp difference differential)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:42
S75	24	(gated adj diode MOS adj capacitor MIS adj capacitor) and sense adj amplifier and invert? and control adj line and signal adj line and (opamp difference differential)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:48
S76	24	(gated adj diode MOS adj capacitor MIS adj capacitor) and sense adj amplifier and invert? and control adj line and signal adj line	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:48
S77	0	gated adj diode.clm. and sense adj amplifier.clm. and signal adj line and control adj line	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 15:23
S78	1	gated adj diode.clm. and (signal sense) adj amplifier.clm.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 15:23

S79	1	gated adj diode.clm. and (signal sense) adj (amplification amplifier).clm.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 15:23
S80	2	gated adj diode.clm. and (signal sense) adj (amplification amplifier amplifying). clm.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:25
S81	1	gated adj diode.clm. and (signal sense) adj (amplification amplifier amplifying). clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:26
S82	1	gated adj diode.clm. and (signal sense) adj (amplification amplifier amplifying).ti, ab.clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:26
S83	1	gated adj diode.ti,ab,clm. and (signal sense) adj (amplification amplifier amplifying).ti,ab,clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:26
S84	3	gated adj diode.ti,ab,clm. and (signal sense) adj (amplification amplifier amplifying).ti,ab,clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:28
S85	1	gated adj diode.ti,ab,clm. and (signal sense) adj amplifier.ti,ab,clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:30
S86	3	gated adj diode near20 (signal sense) adj amplifier	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:31

S87	19	(US-20030123276-\$ or US-20030206437-\$ or US-20040136251-\$ or US-20050099859-\$ or US-20050104118-\$ or US-20050104119-\$ or US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$).did. or (US-4538287-\$ or US-5838176-\$ or US-5844265-\$ or US-6097432-\$ or US-6414862-\$ or US-6418044-\$ or US-6674116-\$ or US-6687175-\$ or US-6731529-\$ or US-6794707-\$).did.	US-PGRUB; USPAT	OR	OFF	2005/08/28 15:56
S88	49076	(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm.	US-PGRUB; USPAT	OR	ON	2005/08/28 15:56
S89	120366	(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm.	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:04
S90	15582	(gated adj diode varactor variable adj (capacitance capacitor)).ti,ab,clm.	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:57
S91	618	S89 and S90	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:02
S92	572	S91 and @ad<"20040106"	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:59
S93	133	S91 and @ad<"20040106" and (invert?r latch buffer)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:59
S94	353	S89 and S90	USPAT	OR	ON	2005/08/28 16:02

S95	4	{(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm. and (gated adj diode).ti,ab,clm.	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:05
S96	4	{(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm. and (gated adj diode).ti,ab,clm. and gated adj diode	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:06
S97	17	{(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm. and gated adj diode	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:10
S98	1	bridge adj demodulat? adj amplifier and gated adj diode	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:13
S99	721	{(variable adj capacitor varactor varactor) and (inverter invertor latch buffer) and (signal sense) adj (amplifier amplification)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:24
S100	721	{(variable adj capacitor varactor varactor) and (inverter invertor latch buffer) and ((signal sense) adj (amplifier amplification) amplifying near2 signal) and (signal sense) adj (amplification amplifier)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:49
S101	920	((327/560) or (327/561) or (327/562) or (327/563)).OCLS	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 16:49

S102	18	S101 and (varact?r variable adj (capacitor capacitance) gated adj diode)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:50
S103	33	(gated adj diode varact?r) near5 (overlap overlapping)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 09:35
S104	47	(gated adj diode varact?r variable adj capacitor).ti,ab,clm. and (overlap overlapping) near6 gate	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 09:35
S105	41	(gated adj diode varact?r variable adj capacitor).ti,ab,clm. and (overlap overlapping) near6 gate not S103	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 09:35
S106	0	365/023	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:11
S107	8592	((365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563) or (257/288) or (257/e29.195)). CCL.S.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/01 17:47
S108	13	S107 and (signal sense) near1 (amplifying amplifier amplification) and (varact?r variable adj capacitor gated adj diode)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:15
S109	15	S107 and (signal sense) near1 (amplifying amplifier amplification) and (varact?r variable adj capacitor gated adj diode)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 12:15

S110	4	"751714".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 18:04
S111	1	(US-20050145895-\$).did.	US-PGPUB	OR	OFF	2006/02/25 18:05
S112	1	(US-20050145895-\$).did.	US-PGPUB	OR	OFF	2006/02/25 18:05
S113	1	S112 and gated adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 18:22
S114	2	("5844265").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 19:35
S115	429	(varactor varactor gated adj diode).ti,ab,clm. and (amplification amplifier amplifying amplify).ti,ab,clm. and capacitance.ti,ab,clm. and @ad<"20040106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 19:37
S116	48	(varactor varactor gated adj diode).ti,ab,clm. and (amplification amplifier amplifying amplify).ti,ab,clm. and capacitance.ti,ab,clm. and @ad<"20040106" and (MOSFET MOS MESFET field adj effect adj (device transistor)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 19:38
S117	8928	((257/288) or (257/e29.195) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563)). CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/22 16:12
S118	2	S115 and S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 19:40

S119	2	*5844265*.pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/01 18:48
S120	180	(varactor varactor) near4 amplifier.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/01 19:16
S121	7	gated adj diode near3 amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/01 19:25
S122	11	gated adj diode with amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/01 19:37
S123	25	mos adj capacitor near2 amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/01 19:37
S124	17	(gated adj diode mos adj capacitor) near4 overlap\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 09:24
S125	5	sti near4 (gated adj diode mos adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 09:31
S126	7	sti near6 (gated adj diode mos adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 09:32



SI27	7	sti near8 (gated adj diode mos adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 09:32
SI28	14	sti with (gated adj diode mos adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 09:33
SI29	6	sti with (gated adj diode mos adj capacitor) and mos adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 09:37
SI30	2	("5844265").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/02 09:46
SI31	5	varactor with (overlap overlapped overlapping) with gate with source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 12:38
SI32	2	("20040263272").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/02 12:40
SI33	9270	((257/288) or (257/e29.195) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563)). COLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/02 12:41
SI34	21	SI33 and (varact?r gate adj diode MOS adj capacitor) near20 (amplifier amplification amplifying)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 12:43
SI35	1	(US-20050145895-\$.)did.	US-PGPUB	OR	OFF	2007/01/22 14:54

SI36	1	(US-20050145895-\$).did. and control adj line	US-PGPUB	OR	ON	2007/01/22 14:57
SI37	0	(US-20050145895-\$).did. and control adj line and coupling adj element	US-PGPUB	OR	ON	2007/01/22 15:00
SI38	1	(US-20050145895-\$).did. and control adj line and coupling and (amplification amplifier)	US-PGPUB	OR	ON	2007/01/22 15:01
SI39	1	(US-20050145895-\$).did. and control adj line and coupling and (amplification amplifier) and control adj signal	US-PGPUB	OR	ON	2007/01/22 15:22
SI40	2	("5844265").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/22 15:22
SI41	0	(257/29.195).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/22 16:11
SI42	0	(257/29.001).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/22 16:12
SI43	172	(257/e29.195).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/22 16:12
SI44	2	("5634208").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/24 08:32
SI45	1	(US-20050145895-\$).did.	US-PGPUB	OR	OFF	2007/05/09 13:32
SI46	1	(US-20050145895-\$).did. and (control adj element control)	US-PGPUB	OR	OFF	2007/05/09 13:37

SI47	2	("5844265").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/09 14:52
SI48	2	("20020098628").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/09 15:10
SI49	57090	gate adj insulating	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 15:10
SI50	1	SI48 and gate adj insulating	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 15:11
SI51	1	SI48 and gate adj insulating near6 (thick thickness)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 19:00
SI52	2148	257/288	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 15:38
SI53	304668	"195"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 15:38
SI54	5297	365/203	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 15:38

SI55	11356	((257/288) or (257/e29.165) or (257/195) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563)).CCLS	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/09 15:40
SI56	19	SI55 and ((circuit near4 (amplifying amplification)) amplifier) and (gated adj diode varact?)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 15:52
SI57	0	"5847583".ap.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 15:52
SI58	2	"5847583".pn.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 18:13
SI59	37	memory adj cell near4 (gated adj diode)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 18:27
SI60	8	memory adj cell near4 (gated adj diode).ti.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/09 18:13
SI61	3	("7116594").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/09 18:27
SI62	1	SI61 and reference adj voltage	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/09 18:27

SI63	11356	((257/288) or (257/e29.165) or (257/195) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563)).CCLS.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 16:29
SI64	5	SI63 and (amplifying amplify amplifier amplification) near6 circuit.clm. and (gated adj diode two\$(terminal).clm.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 16:30
SI65	7	"5844265"	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 11:32
SI66	2	("5844265").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 11:44
SI67	439	varactor near4 (amplifier amplify amplifying)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 11:45
SI68	65	varactor near1 (amplifier amplify amplifying)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 13:19
SI69	3	("7116594").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 13:19
SI70	10897	((257/288) or (257/e29.165) or (257/195) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563)).CCLS.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 16:04

SI71	1013	((327/560) or (327/561) or (327/562) or (327/563)).CQLS.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 16:28
SI72	10897	SI70 SI71	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 16:29
SI73	6	SI72 and (amplifying amplify amplifier amplification) near6 circuit.clm. and (gated adj diode two\$1terminal).clm.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 16:32
SI74	8	(luk near2 wing.in. (international adj business ibm).as.) and (amplifying amplify amplifier amplification) near6 circuit.clm. and (gated adj diode two\$1terminal).clm.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 16:33
SI75	2	"6611106".pn.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 18:24
SI76	2	"4826646".pn.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 18:38
SI77	2	"4268353".pn.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 19:15
SI78	3	("3416110").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 19:16

SI79	2	("3742408").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 19:17
SI80	3	("3978442").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/22 19:19
SI81	105	eddy adj current and tokamak	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/22 19:20
SI82	1	eddy adj current near6 (magnet\$2 field) adj coil and tokamak.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/22 19:20
SI83	1	(US-20050146895-\$).did.	US-PGPUB	OR	ON	2008/01/06 14:05
SI84	971	(amplify\$3 near4 method).ti,ab,clm. and (MOSFET M\$FET gated adj diode field adj effect adj transistor FET JFET MESFET M\$FET)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:08
SI85	4	(amplify\$3 near4 method).ti,ab,clm. and (gated adj diode)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:11
SI86	3	("7116594").PN.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/06 14:13

S187	462	two-terminal adj2 device and (mosfet misfet jfet mesfet field adj effect adj transistor)	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:14
S188	18	two-terminal adj2 device near6 (mosfet misfet jfet mesfet field adj effect adj transistor)	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:32
S189	300	(method near4 amplifying).ti.ab.clm. and (gate adj diode ((mosfet misfet jfet mesfet) near4 ((substrate body) adj bias))	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:34
S190	6	(method near4 amplifying).ti.ab.clm. and (gate adj diode ((mosfet misfet jfet mesfet) near4 ((substrate body) adj bias)))	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:35
S191	387	(amplifier (method near4 amplifying)).ti.ab.clm. and (gate adj diode ((mosfet misfet jfet mesfet) near4 ((substrate body) adj bias)))	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:36
S192	311	(amplifier (method near4 amplifying)).ti.ab.clm. and (gate adj diode ((mosfet misfet jfet mesfet) near4 ((substrate body) adj bias))) and @ad<"20040106"	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 14:44
S193	267	(amplifier (method near4 amplifying)).ti.ab.clm. and (gate adj diode) and @ad<"20040106"	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 15:06



S194	1561	{amplifier (method near4 amplifying)).ti,ab,clm. and (gate adj diode diode-connected adj (MOSFET transistor)) and @ad<"20040106"	US-PG Pub; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 15:07
S195	172	{amplifier (method near4 amplifying)).ti,ab,clm. and (gate adj diode diode-connected adj (MOSFET transistor)) and signal adj line and @ad<"20040106"	US-PG Pub; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 15:07
S196	132	{amplifier (method near4 amplifying)).ti,ab,clm. and (gate adj diode diode-connected adj (MOSFET transistor)) and signal adj line and @ad<"20040106"	USPAT	OR	ON	2008/01/06 15:35
S197	24	{amplifier (method near4 amplifying)).ti. and (gate adj diode diode-connected adj (MOSFET transistor)) and signal adj line and @ad<"20040106"	USPAT	OR	ON	2008/01/06 15:53
S198	1258	bias adj circuit near3 (amplifying amplifier)	USPAT	OR	ON	2008/01/06 15:54
S199	347	bias adj circuit near1 (amplifying amplifier)	USPAT	OR	ON	2008/01/06 15:54
S200	57	bias adj circuit near1 (amplifying amplifier).ti,ab.	USPAT	OR	ON	2008/01/06 15:54
S201	61	gated adj diode and (amplifying amplifier) and mosfet	US-PG Pub; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 15:32
S202	106	(gated adj diode mos adj capacitor) near10 (amplifying amplifier) and (amplifier amplifying).ti,ab,clm.	US-PG Pub; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 15:57
S203	2	("5973974").PN.	US-PG Pub; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/04 16:07

S204	1	S203 and (signal adj line digit adj line)	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 16:17
S205	19	(gated adj diode mos adj capacitor) near10 (amplifying amplifier) and (amplifier amplifying).ti,ab,clm. and (digit signal) adj line	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 16:21
S206	2	("20040071005").PN.	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/04 16:25
S207	0	("senseadj amplifier.ti,ab,clm.and(voltage \$1dependentadj capacitor MOSadj capacitor gated adj diode)"),PN.	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/05 08:26
S208	342	sense adj amplifier.ti,ab,clm. and (voltage\$1dependent adj capacitor MOS adj capacitor gated adj diode)	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 08:27
S209	245	sense adj amplifier.ti,ab,clm. and (voltage\$1dependent adj capacitor MOS adj capacitor gated adj diode) and @ad<"20040106"	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 08:28
S210	16	sense adj amplifier.ti,ab,clm. and (voltage\$1dependent adj capacitor MOS adj capacitor gated adj diode) near20 sense adj amplifier and @ad<"20040106"	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:03

S211	188	((level near3 shift\$3) with capacit\$4) and (327/333.ccls. 326/26.ccls. 326/27.ccls. 326/28.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:30
S212	7	((level near3 shift\$3) with capacit\$4) and (327/333.ccls. 326/26.ccls. 326/27.ccls. 326/28.ccls.) and @ad<"20040106" and sense adj amplifier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:32
S213	0	((level near3 shift\$3) with capacit\$4) and (327/333.ccls. 326/26.ccls. 326/27.ccls. 326/28.ccls.) and @ad<"20040106" and sense adj amplifier and (MOS adj capacitor varactor varacter variable adj capacitor voltage\$1dependent adj capacitor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:38
S214	0	((level near3 shift\$3) with capacit\$4) and (327/333.ccls. 326/26.ccls. 326/27.ccls. 326/28.ccls.) and @ad<"20040106" and sense adj amplifier and (MOS adj capacitor varactor varacter variable adj capacitor voltage\$1dependent near2 capacitor gated adj diode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:39
S215	0	((level near3 shift\$3) near10 capacit\$4) and (327/333.ccls. 326/26.ccls. 326/27.ccls. 326/28.ccls.) and @ad<"20040106" and sense adj amplifier and (MOS adj capacitor varactor varacter variable adj capacitor voltage\$1dependent near2 capacitor gated adj diode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:40
S216	21	((level near3 shift\$3) near10 capacit\$4) and @ad<"20040106" and sense adj amplifier and (MOS adj capacitor varactor varacter variable adj capacitor voltage \$1dependent near2 capacitor gated adj diode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:40
S217	0	((level near3 shift\$3) near10 capacit\$4) and @ad<"20040106" and sense adj amplifier and (MOS adj capacitor varactor varacter variable adj capacitor voltage \$1dependent near2 capacitor gated adj diode) near20 (sense adj amplifier)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:47

S218	53	@ad<"20040106" and sense adj amplifier and (MOS adj capacitor varactor variable adj capacitor voltage\$1dependent near2 capacitor gated adj diode) near20 (sense adj amplifier)	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:48
S219	11	@ad<"20040106" and sense adj amplifier.ti. and (MOS adj capacitor varactor variable adj capacitor voltage\$1dependent near2 capacitor gated adj diode) near20 (sense adj amplifier)	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 09:48
S220	2	jp-10294531\$.\$.did.	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 14:01
S221	2	("6242761").PN.	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/05 14:02
S222	2	("5987048").PN.	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/05 14:09
S223	0	("(chargeadjpumpandMOSadjcapacitor).ti,ab,clm.").PN.	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/05 16:11
S224	90	(charge adj pump and mos adj capacitor).ti,ab,clm.	US-PGRUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/05 16:11

S225	11414	((257/288) or (257/e29.195) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563)). CQLS.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/06 09:44
S226	104	S225 and (method process device apparatus circuit) near3 (amplifying amplification amplifier) and (MOS adj capacitor gated adj diode voltage \$1dependent near2 capacitor varact?) and control near3 signal	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/06 09:47
S227	12663	((250/287) or (257/288) or (257/e29.195) or (365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563) or (330/7)).CQLS.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/06 09:51
S228	104	S226 and (method process device apparatus circuit) near3 (amplifying amplification amplifier) and (MOS adj capacitor gated adj diode voltage \$1dependent near2 capacitor varact?) and control near3 signal	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/06 09:52
S229	4	((international near2 business ibm).as. (luk near1 wing).in. (dennard near1 dennard).in.) and (method process device apparatus circuit) near3 (amplifying amplification amplifier).clm. and (MOS adj capacitor gated adj diode voltage \$1dependent near2 capacitor varact?).clm. and control near3 signal.clm. and (isolat;\$2 near2 device NMOS PMOS NMOSFET PMOSFET MOSFET FET field adj effect).clm.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/06 09:56
S230	4	((international near2 business ibm).as. (luk near1 wing).in. (dennard near1 dennard).in.) and (method process device apparatus circuit) near3 (amplifying amplification amplifier).clm. and (MOS adj capacitor gated adj diode voltage \$1dependent near2 capacitor varact?).clm. and control near3 signal.clm. and (isolat;\$2 near2 device NMOS PMOS NMOSFET PMOSFET MOSFET FET field adj effect).clm.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/06 09:57
S231	2	"5386151".pn.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 08:44

S234	301	signal adj line near3 VDD and (amplification amplifier amplifying)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 08:51
S235	223	signal adj line near2 VDD and (amplification amplifier amplifying)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/16 08:51
S236	112	signal adj line near2 VDD and (amplification amplifier amplifying)	USPAT	OR	ON	2008/08/16 08:51
S237	86	signal adj line near2 VDD and (amplification amplifier amplifying) and @ad<"20040106"	USPAT	OR	ON	2008/08/16 08:53

8/16/2008 11:10:44 AM

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